M.TECH/VLSI/3RD SEM/VLSI 6101/2018 RF IC DESIGN AND MEMS TECHNOLOGY (VLSI 6101)

Time Allotted: 3 hrs Full Marks: 70

Figures out of the right margin indicate full marks.

Candidates are required to answer Group A and <u>any 5 (five)</u> from Group B to E, taking <u>at least one</u> from each group.

Candidates are required to give answer in their own words as far as practicable.

Group – A (Multiple Choice Type Questions)				
1.	Choos	e the correct alternative for	the following:	$10 \times 1 = 10$
	(i)	Due to skin effect, the resista (a) increase (b) decrease		(d) none of the above.
	(ii)	The principle noise arising in (a) flicker noise (b) drain current noise (c) gate noise (d) shot noise.	a MOSFET is due to	
	(iii)	In RF design, it is best to cha (a) current gain (c)power gain	racterize LNAs by their (b) voltage gain (d) trans-resistance ga	ain.
	(iv)	An amplifier senses a sinuscload resistance of 50Ω . The p (a) 1264 μ V (b) 1264 mV	oeak-to-peak voltage sw	-
	(v)	One of the applications of bu (a) SAW sensor (c) temperature sensor	lk micromachining is (b) resonant sens (d) pressure sens	
	(vi)	To design a mixer, which of the following characterizations is not preferred if noise figure is to be taken into account? (a) Current gain (b) Power gain (c) Voltage gain (d) Trans-resistance gain.		
	(vii)	The advantage of the Lab-On (a) it is inexpensive (b) the fluid volume is very s (c) it carries out DNA analys (d) all of the above.	small	

M.TECH/VLSI/3RD SEM/VLSI 6101/2018

(viii)	One of the following body functions is not monitored by the implantable
	sensors:

(a) Glucose for diabetics

(b) Temperature

(c) Heartbeat

(d) Pressure.

(ix) Anodic bonding of a silicon/gas substrate takes place under

(a) high temperature

(b) high pressure

(c) high temperature and pressure

(d) high temperature and high electric voltage.

(x) Which term describes the maximum expected error associated with a measurement or a sensor?

(a) Resolution

(b) Range

(c) Precision

(d) Accuracy

Group - B

2. (a) Highlight the difference between harmonic distortion and intermodulation.

(b) Define the third intercept point and explain why is it a key factor in the design of RF amplifiers?

(c) An LNA senses a -80dBm signal at 2.41 GHz and two -20dBm interferers at 2.42 GHz and 2.43 GHz. What IIP $_3$ is required if the IM products must remain 20 dB below the signal? Assume 50 Ω interfaces at the input and output.

4 + 4 + 4 = 12

3. (a) Discuss a few techniques for designing matching networks in RF VLSI environment.

(b) Suppose we want to match a circuit whose input impedance is R_{in} = 250 Ω to a load having R_L = 50 Ω at an operational frequency of f = 2.45 GHz. Design an appropriate passive matching network to achieve the above situation. List any assumptions you make to arrive at your answer.

(c) Write a short note on passive capacitors and their design considerations.

4 + (4 + 1) + 3 = 12

Group - C

4. (a) Compute the noise figure of a common gate LNA. (Neglect the gate noise)

(b) What do you understand by the feedthrough mechanism in a mixer? Distinguish between single balanced mixers and double balanced mixers.

6 + 6= 12

5. (a) With a neat diagram write the operating principle of a class- F amplifier.

(b) Write a short note on any one of the following

(i) GSM

(ii) CDMA

6 + 6 = 12

Group - D

- 6. (a) Distinguish between micromechanical structures, microsensor, microactuators with distinct examples of each type of structures.
 - (b) What type of unit cell is exhibited by Si crystal?
 - (c) Find the Miller indices of a plane which has intercepts of (3,5,6) in the (a,b,c) crystallographic axes respectively.
 - (d) What is epitaxial growth of Si? Give proper chemical equation to illustrate the deposition process.

$$6 + 2 + 2 + 2 = 12$$

- 7. (a) Differentiate between dry etching and wet etching in bulk micromachining process.
- (b) Explain the method of sol-gel deposition and state its applications.

$$6 + 6 = 12$$

Group - E

- 8.(a) Distinguish between parallel plate and interdigited comb capacitor with respect to configurations and basic working principle as a sensor when realized in MEMS technology.
 - (b) Draw neat diagrams of a membrane switch in open and closed state. Also describe the working principle of such a switch in both the states.

$$6 + 6 = 12$$

- 9.(a) What is a pressure sensor?
- (b) Describe the working principle and structure of a piezoresistive pressure sensor.
- (c) Explain the working principle of a gas sensor.
- (d) Distinguish between electrophoretic flow and electroosmotic flow.

$$2 + 5 + 2 + 3 = 12$$